

AMENDMENTS TO THE SPECIFICATION

Please replace the last paragraph bridging pages 3 and 4 with the following rewritten paragraph:

The metal-polishing composition as described in Japanese Patent Application Laid-Open (Kokai) No. ~~8-837808-83980~~ containing benzotriazole effectively provides a flat surface and prevents dishing. However, polishing rate detrimentally decreases due to strong anti-corrosion effect of benzotriazole. The polishing composition as described in Japanese Patent Application Laid-Open (Kokai) No. 9-55363 containing 2-quinolinecarboxylic acid is not preferred for industrial use, since 2-quinolinecarboxylic acid is a remarkably expensive material.

Please replace the sixth paragraph on page 7 with the following rewritten paragraph:

[14] The polishing composition as recited in [12] or [13] above, wherein the surfactant is at least one species selected from the group consisting of an alkylaromatic-sulfonic acid or a salt thereof, polyoxyethylene alkyl phosphoric acid or a salt thereof, alkyl phosphoric acid or a salt thereof, and a fatty acid or a salt thereof.

Please replace the seventh paragraph on page 7 with the following rewritten paragraph:

[15] The polishing composition as recited in any one of [12] to [14] above, wherein the content of the surfactant is in a range of 5 mass% or less.

Please replace the first paragraph on page 8 with the following rewritten

paragraph:

[18] The polishing composition as recited in any one of [1] to [17] above, wherein the protective-film-forming agent comprises at least one species selected from the group consisting of benzotriazole, tolyltriazole, hydroxybenzotriazole, carboxybenzotriazole, benzimidazole, tetrazole, and quinaldinic acid.

Please replace the second paragraph on page 8 with the following rewritten

paragraph:

[19] The polishing composition as recited in [18] ~~or [19]~~ above, wherein the content of the protective-film-forming agent is in a range of 10 mass % or less.

Please replace the fifth paragraph on page 8 with the following rewritten

paragraph:

[22] The polishing composition as recited in [20] or [21] above, wherein the content of the alkali substance is in a range of 10 mass% or less.

Please replace the eighth paragraph on page 8 with the following rewritten

paragraph:

[25] The polishing composition as recited in any one of [1] to [24]~~[23]~~ above, wherein the content of the abrasive is in a range of 30 mass% or less.

Please replace the last paragraph bridging pages 8 and 9 with the following

rewritten paragraph:

[28] The polishing composition as recited in any one of [1] to ~~[27]~~[26] above, wherein a ratio (P_{RR}/B_{RR}), between a metal film polishing rate (P_{RR}) for polishing a metal film formed on a substrate having trenches such that the metal film fills the trenches, or polishing a metal film formed on a substrate having trenches and a barrier metal film formed on the substrate such that the metal film fills the trenches, and a metal film polishing rate (B_{RR}) for polishing a flat blanket metal film, is 3.5 or more.

Please replace the third full paragraph on page 9 with the following rewritten paragraph:

[31] A polishing method comprising forming a metal film provided on the substrate having trenches such that the metal film fills the trenches, by use of the polishing composition as set forth in any one of [1] to ~~[28]~~[27] above.

Please replace the fourth full paragraph on page 9 with the following rewritten paragraph:

[32] A polishing method comprising forming a barrier metal film on a substrate having trenches, and polishing, by use of the polishing composition as recited in any one of [1] to ~~[28]~~[27] above, a metal film provided on the substrate such that the metal film fills the trenches.

Please replace the fifth full paragraph on page 9 with the following rewritten paragraph:

[33] A polishing method comprising a metal film, wherein a metal film formed on a substrate having trenches such that the metal film fills the trenches, or a metal film formed on a substrate having trenches and a barrier metal film formed on the substrate such that the metal

film fills the trenches, has protrusions, and corners of the protrusions are preferentially polished by the composition as ~~set~~^{set} forth in any one of [1] to ~~[28]~~^[27] above.

Please replace the third full paragraph on page 10 with the following rewritten paragraph:

[37] The method for producing a substrate, the method comprising a step of polishing, through the polishing method as recited in any one of [31] to ~~[33]~~^[36] above, a metal film provided on a substrate having trenches such that the metal film fills the trenches.

Please replace the first full paragraph on page 29 with the following rewritten paragraph:

Molecular weight of each of the synthesized compounds was determined through gel permeation chromatography (GPC) (reduced to polyethylene glycol). In the present invention, a commercial product was also employed, and molecular weight of the commercial product was also determined. The employed commercial product was VPI55K18P (hereinafter abbreviated as 18P) (1-vinylimidazole-1-vinylpyrrolidone (1:1) copolymer, product of BASF) and VPI55K72W (hereinafter abbreviated as ~~72W~~^{18P}, product of BASF).

Please replace the paragraph on page 42 with the following rewritten paragraph:

The results are shown in Table 6. The rate of polishing tantalum barrier film decreased and erosion was more prevented, as increase in amount of azole ~~18PP~~¹⁸. However, since addition of ~~18PP~~¹⁸ in an excessive amount was prone to increase copper polishing rate, step reduction and dishing prevention effect tended to be impaired to degrees slightly higher than

those of Comparative Example 3 employing no 18PP18. Therefore, the amount of 18PP18 is required to be appropriately modified to attain well balance in the composition.

Please replace the last paragraph bridging pages 50 and 51 with the following rewritten paragraph:

DBS stands for dodecyl benzene sulphate, BTA benzotriazole, and THFA ~~tetrahydrofurfuryl~~ tetrahydrofuryl amine. ~~The~~ The colloidal silica used has a particle size of 70-80nm.

Please replace Table 14 on page 56 with the following new Table 14:

Table 14

Ex. Com.Ex.	Polishing Pressure	<u>Cu</u> <u>(blanket)</u> <u>polishing</u> <u>rate</u> B _{RR}	<u>Cu</u> <u>(pattern)</u> <u>polishing</u> <u>rate</u> P _{RR}	P _{RR} /B _{RR}	Step reduction	Dishing
Ex.32	14 kPa	130 nm/min	550 nm/min	4.23	AA	50-60nm
Ex.33	10 kPa	110 nm/min	450 nm/min	4.09	AA	40-60nm
Ex.34	20 kPa	140 nm/min	630 nm/min	4.50	AA	70-80nm